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Contents

Preface vii
Committees/Sponsors viii
Contents ix

Section 1. Deposition methods and growth mechanisms

Electron beam-assisted formation of silicon oxynitride layers (3.5 nm) on silicon at moderate temperatures using NO gas: growth kinetics and mechanisms
P. Poveda and A. Glachant 1

Low-energy vibrational dynamics of hydrogenated silica gels
A. Bartolotta, G. Carini, G. D'Angelo, A. Fontana, F. Rossi and G. Tripodo 9

Silica-based sol–gel films optically functionalized through doping with organic molecules
F. De Matteis, P. Prosposito, F. Sarcinelli, M. Casalboni, R. Pizzoferrato, A. Furlani, M.V. Russo, A. Vannucci and M. Varasi 15

Properties of SiO_2 films deposited on silicon at low temperatures by plasma enhanced decomposition of hexamethyldisilazane
A. Pêcheur, J.L. Autran, J.P. Lazarri and P. Pinard 20

Section 2. Electrical characterization

On the use of dielectric films in temperature measurements: application to the realization of capacitive thermometers for temperatures < 5 K
D. Boutard-Gabillet, P. Aranda, F. Ladieu, P. Pari and M. Rotter 27

Effect of boron penetration on the stress induced leakage current in PMOS structures with p+ doped polysilicon gate
C. Jahan and K. Barla 33

Stress induced leakage currents in *N*-MOSFETs submitted to channel hot carrier injections
D. Goguenheim, A. Bravaix, D. Vuillaume, F. Mondon, M. Jourdain and A. Meinertzhagen 41

Electric field and temperature dependence of the stress induced leakage current: Fowler–Nordheim or Schottky emission?
P. Riess, G. Ghibaudo, G. Pananakakis, J. Brini and G. Ghidini 48

Electrical properties of oxynitride thin films using noise and charge pumping measurements
P. Masson, P. Morfouli, J.L. Autran, J. Brini, B. Balland, E.M. Vogel and J.J. Wortman 54

Study of hot carrier degradation in dram cells combining random telegraph signal and charge pumping measurements
S. Pierunek, D. Pogany, J.L. Autran and B. Leroy 59

On the correlation between interface defects, positive oxide charge and hole fluence throughout the oxide
F. Nebel and M. Jourdain 67

Theoretical and experimental study of the conduction mechanism in $Al/Ta_2O_5/SiO_2/Si$ and $Al/Ta_2O_5/Si_3N_4/Si$ structures
C. Chaneliere, J.L. Autran, S. Four, R.A.B. Devine and B. Balland 73

Reverse short and narrow channel effects in n and p transistors: quantification of the enhanced diffusion and the gate oxide thickness increase
B. Leroy, P.H. Albarede and P. Martin 79
Dynamic stressing of thin tunnel oxides: a way to emulate a single EEPROM cell programming function
C. Plossu, J.M. Voisin, B. Bos, C. Raynaud, R. Bouchakour, P. Boivin and B. Balland 85
On the electrical conductivity in porous silicon under light and electron beams
A.S. Dafinei and A.A. Dafinei 92
Influence of polycide deposition on the reliability of wet and nitrided oxides
K. Yckache, P. Boivin, F. Baiget, C. Kristukat, G. Auriel, B. Sagnes, J. Oualid and A. Glachant 97
Investigation of low field and high temperature SiO_2 and ONO leakage currents using the floating gate technique
B. De Salvo, G. Ghibaudo, G. Pananakakis and B. Guillaumot 104

Section 3. Optoelectronics

Defect radial repartitions in ultraviolet irradiated germanosilicate optical fibres
F. Goutaland, A. Boukenter and Y. Ouerdane 110
Terbium(III) doped silica-xerogels: effect of aluminium(III) co-doping
C. Armellini, M. Ferrari, M. Montagna, G. Pucker, C. Bernard and A. Monteil 115
Synthesis of silver clusters in silica-based glasses for optoelectronics applications
E. Borsella, E. Cattaruzza, G. De Marchi, F. Gonella, G. Mattei, P. Mazzoldi, A. Quaranta, G. Battaglin and R. Polloni 122
Optical spectroscopy of Pr^{3+} ions in sol–gel derived GeO_2–SiO_2 planar waveguides
C. Duverger, M. Ferrari, C. Mazzoleni, M. Montagna, G. Pucker and S. Turrell. 129
Active waveguides in ferroelectric crystals by ion exchange
F. Caccavale, C. Sada, F. Segato, Yu.N. Korkishko, V.A. Fedorov and T.V. Morozova 135
Structural properties and photoluminescence spectra of coloured LiF films on SiO_2
L. Fornarini, A. Mancini, S. Martelli, R.M. Montereali, P. Picozzi and S. Santucci 141

Section 4. Electronic and atomic structure

Study of oxygen vacancies in silica using ultra soft pseudopotentials
N. Capron, S. Carniato, G. Boureau and A. Pasturel 146
(100) Silicon oxidation: first principle investigation of basic mechanisms
A. Estève, M. Djafari Rouhani and D. Estève 150
Theoretical study using density functional theory of defects in amorphous silicon dioxide
A. Courtot-Descharles, P. Paillet and J.L. Leray 154
Mid-gap states in the forbidden gap of silica
S.A. Prosandeyev, G. Boureau and S. Carniato. 161

Section 5. Point defects

Electron paramagnetic resonance spectra of interface defects in nitric oxide treated Si/SiO_2
H.J. von Bardeleben, J.L. Cantin, L.G. Gosset, J.J. Ganem, I. Trimaille and S. Rigo. 169
Infra-red, electron paramagnetic resonance and X-ray photoemission spectral properties of point defects in silica from first-principle calculations
G. Pacchioni and M. Vitiello. 175
Vacuum ultraviolet absorption of silica samples
A. Anedda, C.M. Carbonaro, R. Corpino and A. Serpi. 183
Photoluminescence activity in natural silica excited in the vacuum-UV range
M. Cannas, M. Barbera, R. Boscaino, A. Collura, F.M. Gelardi and S. Varisco 190
The landscape of the excitation profiles of the α_E and β emission bands in silica
M. Leone, R. Boscaino, M. Cannas and F.M. Gelardi 196

Section 6. Analytical methods

Thermal conductivity of SiO_2 films by scanning thermal microscopy
S. Callard, G. Tallarida, A. Borghesi and L. Zanotti 203
Surface morphology of nitrided thin thermal SiO_2 studied by atomic force microscopy
G. Tallarida, F. Cazzaniga, B. Crivelli, R. Zonca and M. Alessandri 210
Temperature effects on the Si/SiO_2 interface defects and suboxide distribution
F. Jolly, J.L. Cantin, F. Rochet, G. Dufour and H.J. von Bardeleben 217
Properties of stacked dielectric films composed of $SiO_2/Si_3N_4/SiO_2$
S. Santucci, L. Lozzi, M. Passacantando, A.R. Phani, E. Palumbo, G. Bracchitta, R. De Tommasis, A. Torsi, R. Alfonsetti and G. Moccia 224

Section 7. Defect generation and transformation

Low-field current on thin oxides after constant current or radiation stresses
M. Ceschia, A. Paccagnella, A. Cester, A. Scarpa, A. Candelori and G. Ghidini 232
Electron irradiation effects on thin MOS capacitors
A. Candelori, A. Paccagnella, M. Cammarata, G. Ghidini and M. Ceschia 238

Author index 245
Subject index 249